AMENDMENTS

IN THE CLAIMS:

Please cancel claims 20-29 as follows:

1. (Original) A system for depositing films on semiconductor wafers comprising:

a deposition chamber;

an acoustic microbalance configured for mounting within the deposition chamber, and

a controller;

wherein the controller is configured to provide feedback control based on data provided at least in part by the acoustic microbalance.

- 2. (Original) The system of claim 1, wherein the system is configured for sequential batch operation and the controller controls one or more process conditions for a batch based, at least in part, on data obtained from a preceding batch.
- 3. (Original) The system of claim 2, wherein the controller detects a deposition process endpoint based, at least in part, on data provided by the acoustic microbalance.
- 4. (Original) The system of claim 1, wherein the feedback control is over an active deposition process, whereby one or more process conditions in the active process are selectively modified.
- 5. (Original) The system of claim 4, wherein the controller comprises a computer system component that encodes a probabilistic dependancy model relating a set of input variables that includes at least a measurement from the acoustic microbalance to one or more outputs

that relate to an effect of modifying one or more process conditions.

- 6. (Original) The system of claim 1, wherein the acoustic microbalance is mounted on one of the semiconductor wafers.
- 7. (Original) The system of claim 1, wherein the acoustic microbalance is mounted on a control wafer.
- 8. (Original) The system of claim 1, wherein the acoustic microbalance is a surface acoustic wave device.
- 9. (Original) The system of claim 1, wherein the acoustic microbalance comprises a quartz crystal.
- 10. (Original) A system for depositing films on semiconductor wafers comprising:

a deposition chamber;

an acoustic microbalance having a cantilever and configured for mounting within the deposition chamber; and

a controller;

wherein the controller is configured to detect the endpoint of a deposition process based on data provided at least in part by the acoustic microbalance; and

the controller comprises a computer system component that encodes a model or database that accounts for a difference between an extent of deposition on the cantilever and an extent of deposition on the semiconductor wafers.

11. (Original) The system of claim 10, wherein the computer system component encodes a probabilistic dependancy model that the computer system

employs in accounting for the difference between the extent of deposition on the cantilever and the extent of deposition on the semiconductor wafers

- 12. (Original) The system of claim 10, wherein the controller is configured to provide feedback control based on data provided at least in part by the acoustic microbalance.
- 13. (Original) The system of claim 10, wherein the system is configured for sequential batch operation and the controller controls one or more process conditions for a batch based, at least in part, on data obtained from a preceding batch.
- 14. (Original) The system of claim 10, wherein the controller is configured to exercise feedback control over one or more process conditions.
- 15. (Original) The system of claim 14, wherein the controller comprises a computer system component that encodes a probabilistic dependancy model relating a set of input variables that includes at least a measurement from the acoustic microbalance to one or more outputs that relate to the effect modifying one or more process conditions.
- 16. (Original) The system of claim 10, wherein the acoustic microbalance is mounted on one of the semiconductor wafers.
- 17. (Original) The system of claim 10, wherein the acoustic microbalance is mounted on a control wafer.
- 18. (Original) The system of claim 10, wherein the acoustic microbalance is a surface acoustic wave device.

- 19. (Original) The system of claim 10, wherein the acoustic microbalance comprises a quartz crystal.
 - 20-29. (Canceled).